

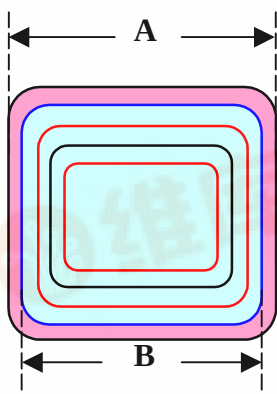


CMS-S087-060

SCHOTTKY BARRIER DIODE

Features :

- * Extremely low forward volts
- * Guard ring protection
- * Low reverse leakage current



Chip size(A): 2.210* 2.210 mm²

Bond Pad size(B) : 2.083 *2.083 mm²

Thickness : 300μm ± 20μm

Metalization : Anode Ti/Ni/Ag

Metalization : Cathode Ti/Ni/Ag

Electrical Characteristics	Sym.	Spec. Limit	Unit
Maximum Instantaneous Forward Volt at IF : 8.0Amp. 25°C	VF max	0.73	Volt
Minimum Instantaneous Reverse Voltage at IR : 300 uA 25°C	VR min.	63	Volt.
Minimum Non-repetitive Peak Surge current at 25°C	IFSM	150	Amp
Storage Temperature	TSTG	-65 to +125	°C

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